# 60V NPN LOW SATURATION MEDIUM POWER TRANSISTOR IN E-LINE

#### **SUMMARY**

 $BV_{CEO}$  = 60V :  $R_{SAT}$  = 34m $\Omega$ ;  $I_{C}$  = 4.5A

#### **DESCRIPTION**

Packaged in the E-line outline this new 5th generation low saturation 60V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

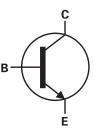
# E-LINE

# **FEATURES**

- Externely low equivalent on-resistance;  $R_{SAT}$  = 34m $\Omega$  at 5A
- 4.5 amps continuous current
- Up to 15 amps peak current
- · Very low saturation voltages

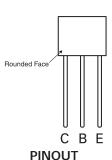
## **APPLICATIONS**

- Emergency lighting circuits
- Motor driving (including DC fans)
- Solenoid, relay and actuator drivers
- DC modules
- Backlight inverters



#### ORDERING INFORMATION

DEVICE	QUANTITY	
ZX5T851ASTOA	2000 units / reel	
ZX5T851ASTZ	2000 units / carton	



## **DEVICE MARKING**

• X5T851

**ZETEX** 

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# **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV <sub>CBO</sub>	150	V
Collector-emitter voltage	BV <sub>CEO</sub>	60	V
Emitter-base voltage	BV <sub>EBO</sub>	7	V
Continuous collector current (a)	I <sub>C</sub>	4.5	А
Peak pulse current	I <sub>CM</sub>	15	А
Practical power dissipation <sup>(a)</sup>	P <sub>D</sub>	1.0	W
Linear derating factor		8	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	0.71	W
Linear derating factor		5.7	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

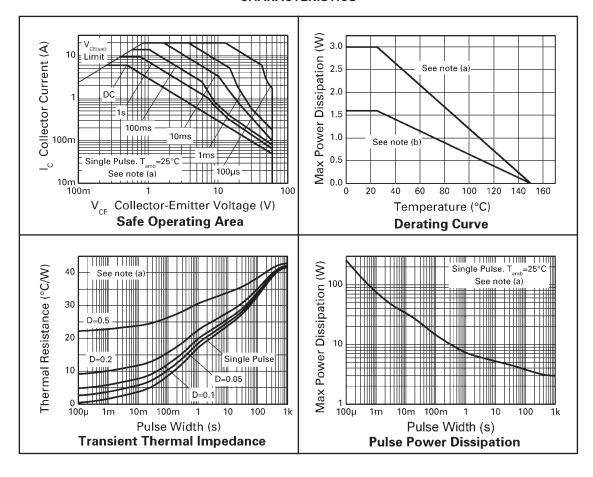
# THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	125	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	175	°C/W



 <sup>(</sup>a) For a device through hole mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. Collector lead length to solder point 4mm.
(b) For a device mounted in a socket in still air conditions. Collector lead length 10mm.

#### **CHARACTERISTICS**



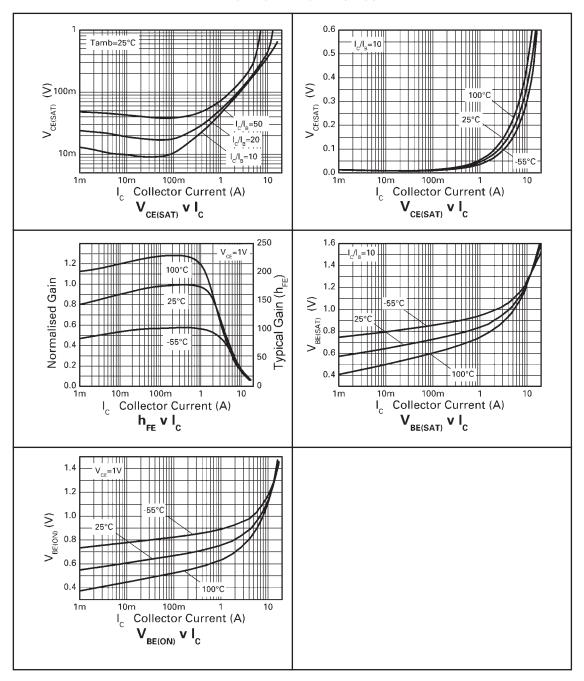
# **ELECTRICAL CHARACTERISTICS** (at T<sub>amb</sub> = 25°C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV <sub>CBO</sub>	150	190		V	I <sub>C</sub> =100μA
Collector-emitter breakdown voltage	BV <sub>CER</sub>	150	190		V	I <sub>C</sub> =1μA, RB≤1kΩ
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	60	80		V	I <sub>C</sub> =10mA*
Emitter-base breakdown voltage	BV <sub>EBO</sub>	7	8.1		V	I <sub>E</sub> =100μA
Collector cut-off current	I <sub>CBO</sub>			20	nA	V <sub>CB</sub> =120V
				0.5	μΑ	V <sub>CB</sub> =120V, T <sub>amb</sub> =100°C
Collector cut-off current	I <sub>CER</sub>			20	nA	V <sub>CB</sub> =120V
	$R \le 1k\Omega$			0.5	μΑ	V <sub>CB</sub> =120V, T <sub>amb</sub> =100°C
Emitter cut-off current	I <sub>EBO</sub>			10	nA	V <sub>EB</sub> =6V
Collector-emitter saturation voltage	V <sub>CE(SAT)</sub>		18	30	mV	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA*
			40	55	mV	I <sub>C</sub> =1A, I <sub>B</sub> =100mA*
			45	65	mV	I <sub>C</sub> =1A, I <sub>B</sub> =50mA*
			95	130	mV	I <sub>C</sub> =2A, I <sub>B</sub> =50mA*
			170	210	mV	I <sub>C</sub> =5A, I <sub>B</sub> =200mA*
Base-emitter saturation voltage	V <sub>BE(SAT)</sub>		950	1050	mV	I <sub>C</sub> =4A, I <sub>B</sub> =200mA*
Base-emitter turn-on voltage	V <sub>BE(ON)</sub>		840	950	mV	I <sub>C</sub> =4A, V <sub>CE</sub> =1V*
Static forward current transfer ratio	h <sub>FE</sub>	100	200			I <sub>C</sub> =10mA, V <sub>CE</sub> =1V*
		100	200	300		I <sub>C</sub> =2A, V <sub>CE</sub> =1V*
		55	105			I <sub>C</sub> =5A, V <sub>CE</sub> =1V*
		20	40			I <sub>C</sub> =10A, V <sub>CE</sub> =1V*
Transition frequency	f <sub>T</sub>		130		MHz	I <sub>C</sub> =100mA, V <sub>CE</sub> =10V
						f=50MHz
Output capacitance	СОВО		31		pF	V <sub>CB</sub> =10V, f=1MHz*
Switching times	t <sub>ON</sub>		42		ns	I <sub>C</sub> =1A, V <sub>CC</sub> =10V,
	t <sub>OFF</sub>		760		ns	I <sub>B1</sub> =I <sub>B2</sub> =100mA

<sup>\*</sup> Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ ; duty cycle  $\leq 2\%$ .



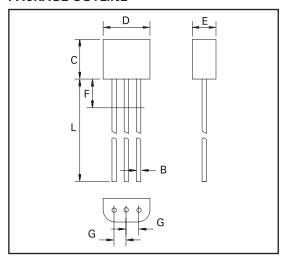
#### **TYPICAL CHARACTERISTICS**



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# **PACKAGE OUTLINE**



Controlling dimensions are in millimeters. Approximate conversions are given in inches

# PACKAGE DIMENSIONS

DIM -	Millimeters		Inches		
	Min	Max	Min	Max	
Α	0.41	0.495	0.016	0.0195	
В	0.41	0.495	0.016	0.0195	
С	3.61	4.01	0.142	0.158	
D	4.37	4.77	0.172	0.188	
Е	2.16	2.41	0.085	0.095	
F	_	2.50	_	0.098	
G	1.27 NOM		0.050	NOM	
L	13.00	13.97	0.512	0.550	

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Europe		Americas	Asia Pacific
Zetex plc	Zetex GmbH	Zetex Inc	Zetex (Asia) Ltd
Fields New Road	Streitfeldstraße 19	700 Veterans Memorial Hwy	3701-04 Metroplaza Tower 1
Chadderton	D-81673 München	Hauppauge, NY 11788	Hing Fong Road
Oldham, OL9 8NP		•	Kwai Fong
United Kingdom	Germany	USA	Hong Kong
Telephone (44) 161 622 4444	Telefon: (49) 89 45 49 49 0	Telephone: (1) 631 360 2222	Telephone: (852) 26100 611
Fax: (44) 161 622 4446	Fax: (49) 89 45 49 49 49	Fax: (1) 631 360 8222	Fax: (852) 24250 494
hq@zetex.com	europe.sales@zetex.com	usa.sales@zetex.com	asia.sales@zetex.com

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